



HLB122I

NPN Triple Diffused Planar Type High Voltage Transistor

Description

The HLB122I is a medium power transistor designed for use in switching applications.

Features

- High breakdown voltage
- Low collector saturation voltage
- Fast switching speed

Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$)

- Maximum Temperatures
Storage Temperature $-55 \sim +150^{\circ}\text{C}$
Junction Temperature $+150^{\circ}\text{C}$
- Maximum Power Dissipation
Total Power Dissipation ($T_C=25^{\circ}\text{C}$) 20 W
- Maximum Voltages and Currents
 BV_{CBO} Collector to Base Voltage 600 V
 BV_{CEO} Collector to Emitter Voltage 400 V
 BV_{EBO} Emitter to Base Voltage 6 V
 I_C Collector Current (DC) 800 mA
 I_C Collector Current (Pulse) 1600 mA
 I_B Base Current (DC) 100 mA
 I_B Base Current (Pulse) 200 mA

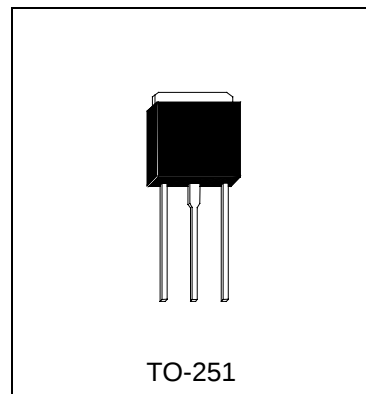
Electrical Characteristics ($T_A=25^{\circ}\text{C}$)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	600	-	-	V	$I_C=100\mu\text{A}$
BV_{CEO}	400	-	-	V	$I_C=10\text{mA}$
BV_{EBO}	6	-	-	V	$I_E=10\mu\text{A}$
I_{CBO}	-	-	10	μA	$V_{CB}=600\text{V}$
I_{CEO}	-	-	10	μA	$V_{CE}=400\text{V}$
I_{EBO}	-	-	10	μA	$V_{EB}=6\text{V}$
$*V_{CE(sat)1}$	-	-	400	mV	$I_C=100\text{mA}$, $I_B=20\text{mA}$
$*V_{CE(sat)2}$	-	-	800	mV	$I_C=300\text{mA}$, $I_B=60\text{mA}$
$*V_{BE(sat)}$	-	-	1	V	$I_C=100\text{mA}$, $I_B=20\text{mA}$
$*h_{FE1}$	10	-	40		$V_{CE}=10\text{V}$, $I_C=0.1\text{A}$
$*h_{FE2}$	10	-	-		$V_{CE}=10\text{V}$, $I_C=0.5\text{A}$
tf	-	-	0.6	μS	$V_{CC}=100\text{V}$, $I_C=0.3\text{A}$, $I_{B1}=-I_{B2}=0.06\text{A}$

*Pulse Test: Pulse Width $\leq 380\mu\text{s}$, Duty Cycle $\leq 2\%$

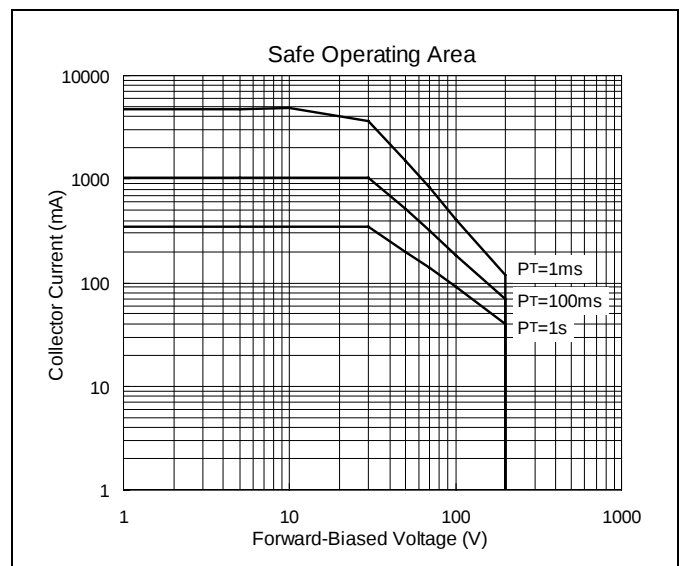
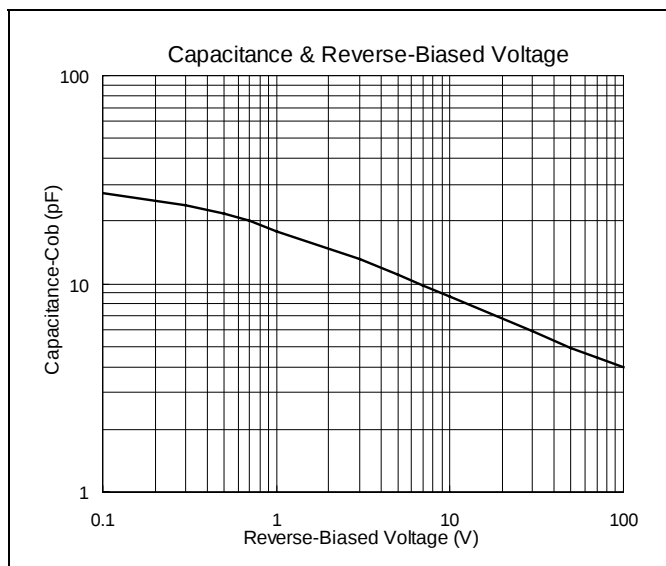
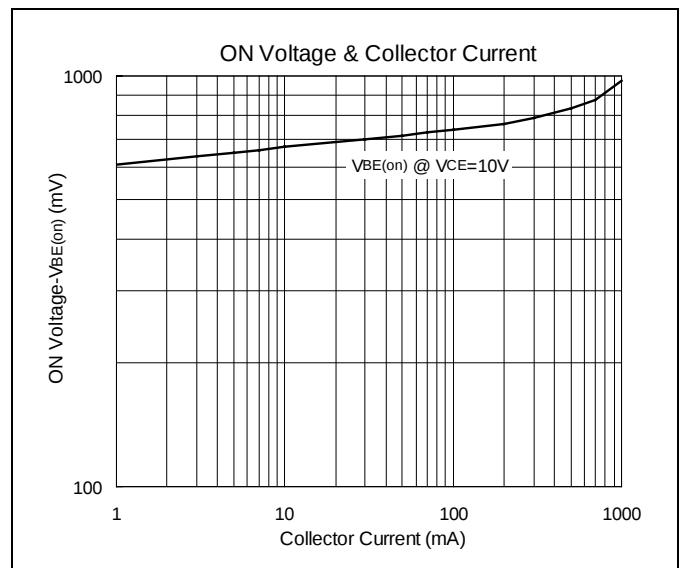
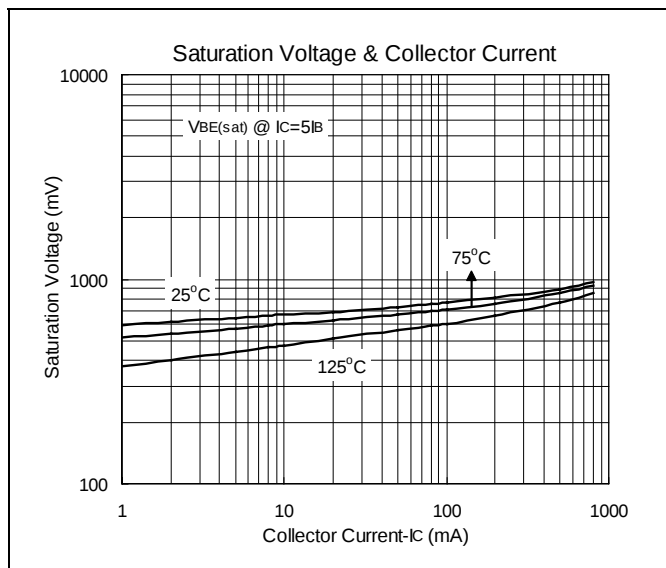
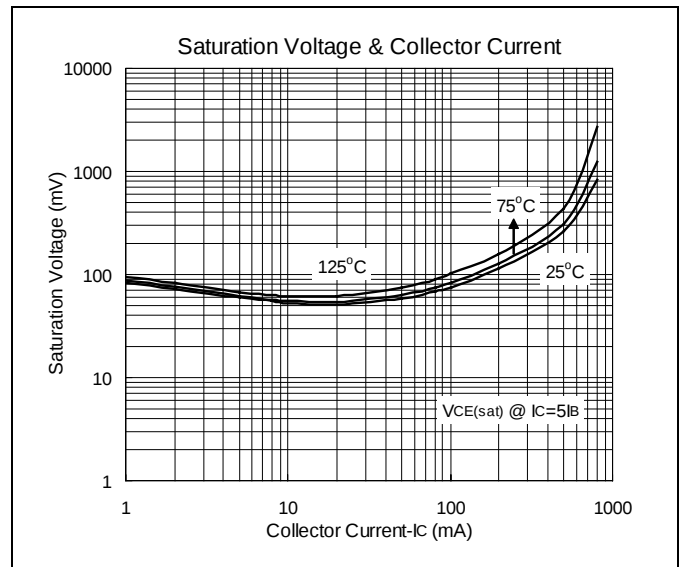
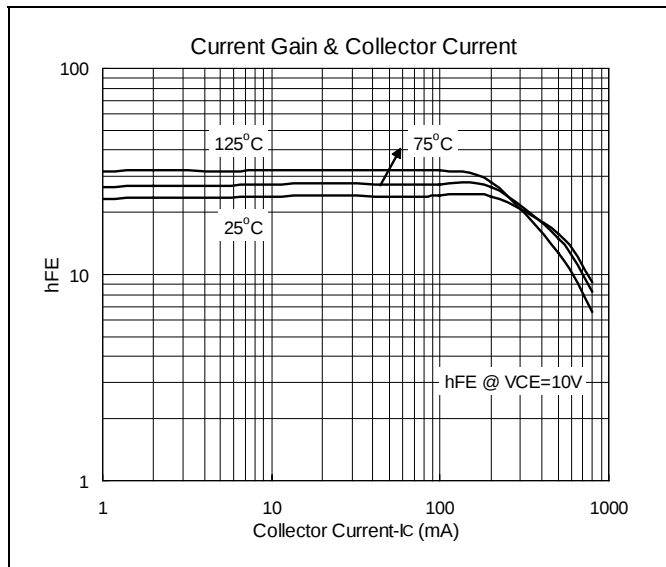
Classification of h_{FE1}

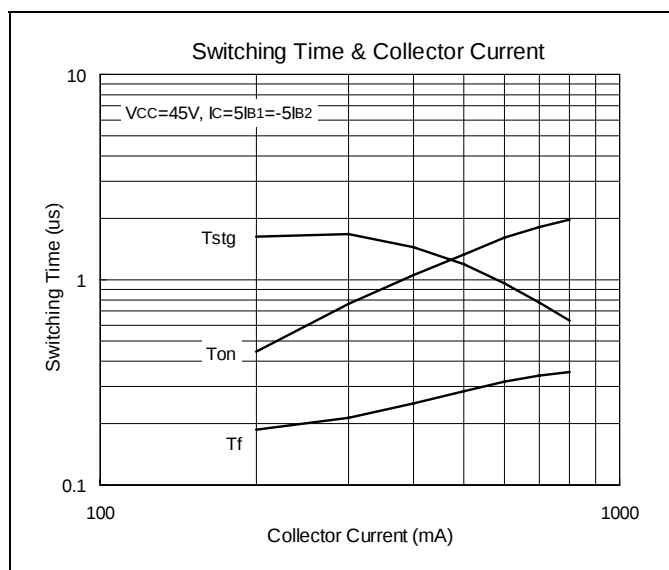
Rank	B1	B2	B3	B4	B5	B6
Range	10-17	13-22	18-27	23-32	28-37	33-40





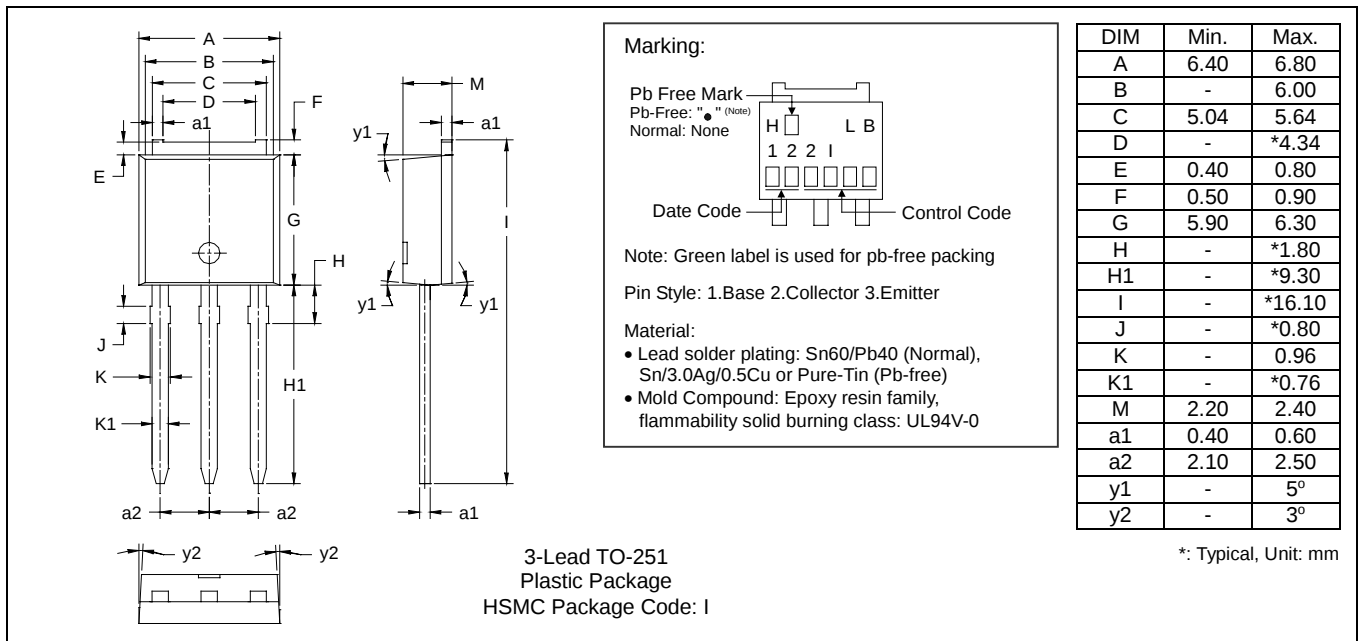
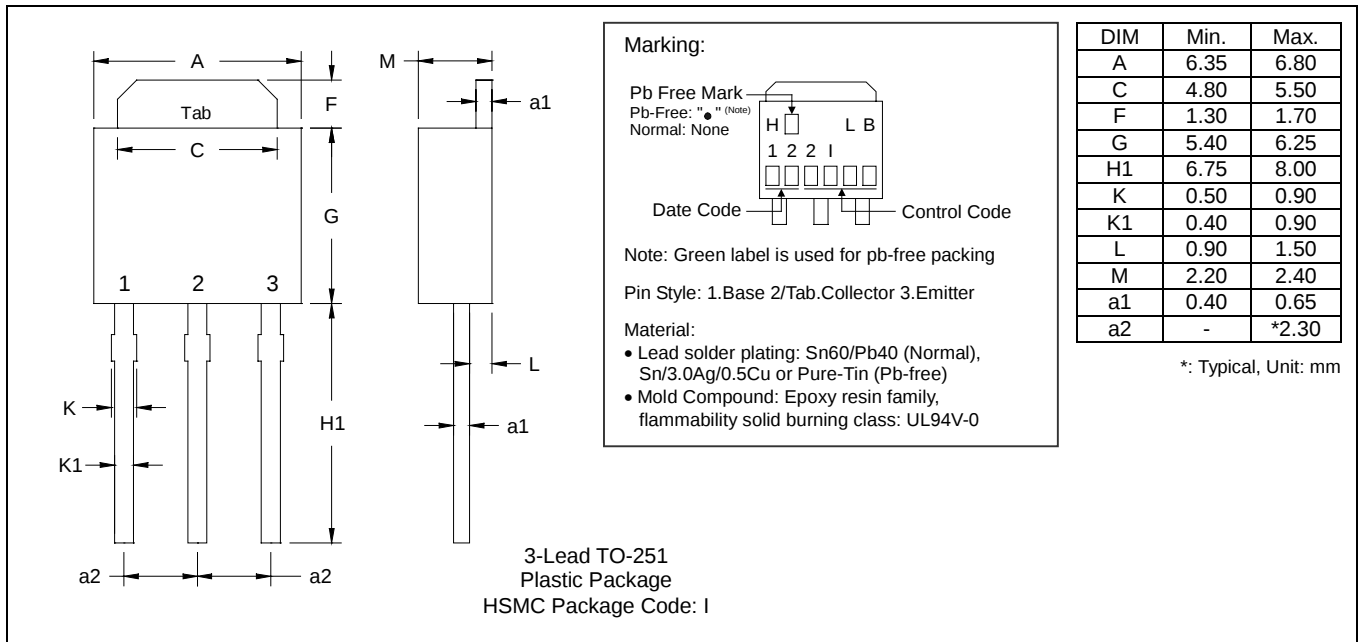
Characteristics Curve







TO-251 Dimension



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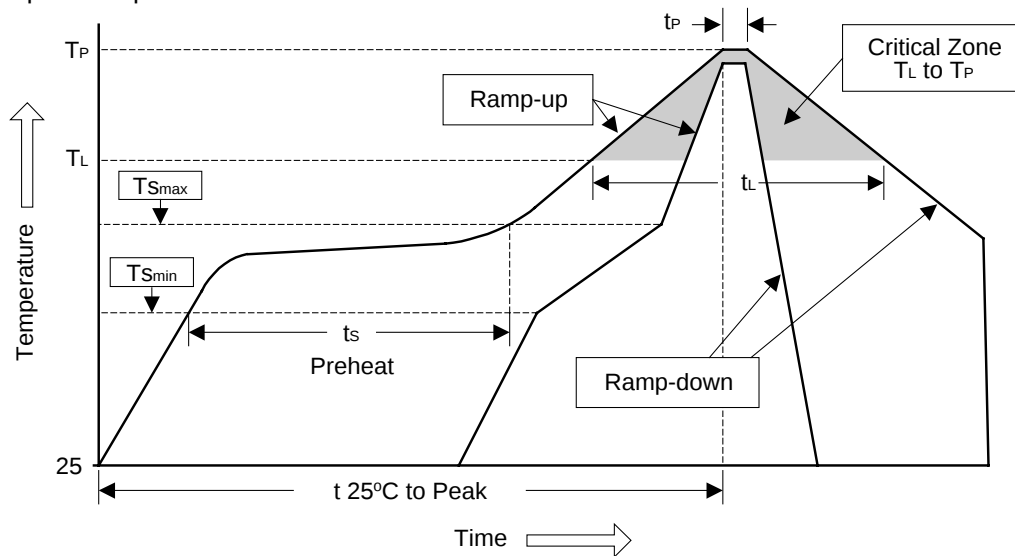
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Soldering Methods for HSMC's Products

1. Storage environment: Temperature=10°C~35°C Humidity=65%±15%
2. Reflow soldering of surface-mount devices

Figure 1: Temperature profile



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (T_{Smin})	100°C	150°C
- Temperature Max (T_{Smax})	150°C	200°C
- Time (min to max) (t_s)	60~120 sec	60~180 sec
T_{Smax} to T_L		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T_L)	183°C	217°C
- Time (t_L)	60~150 sec	60~150 sec
Peak Temperature (T_P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature (t_P)	10~30 sec	20~40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak temperature	Dipping time
Pb devices.	245°C ±5°C	10sec ±1sec
Pb-Free devices.	260°C ±5°C	10sec ±1sec